



SOT-89-3L Plastic-Encapsulate Transistors

PXT3906

TRANSISTOR (PNP)

FEATURES

- Compliment to PXT3904
- Low current
- Low voltage

MARKING: 2A

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

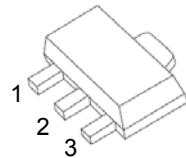
Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _c	Collector Current -Continuous	-0.2	A
P _c	Collector Power Dissipation	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

SOT-89-3L

1. BASE

2. COLLECTOR

3. Emitter

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =-10μA,I _e =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =-1mA,I _b =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =-10μA,I _c =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V,I _e =0			-0.05	μA
9a JH Yf cut-off current	I _{EBO}	V _{EB} =-6V,I _c =0			-0.01	μA
7 c`YWcf W Hc ZW ffYbh	I _{C0Y}	V _{CB} =-30V,X ₀₀ =-MEXA		0.01	0.05	mA
DC current gain	h _{FE(1)}	V _{CE} =-1V,I _c =-0.1mA	60			
	h _{FE(2)}	V _{CE} =-1V,I _c =-1mA	80			
	h _{FE(3)}	V _{CE} =-1V,I _c =-10mA	100		300	
	h _{FE(4)}	V _{CE} =-1V,I _c =-50mA	60			
	h _{FE(5)}	V _{CE} =-1V,I _c =-100mA	30			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _c =-10mA,I _b =-1mA			-0.25	V
	V _{CE(sat)2}	I _c =-50mA,I _b =-5mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)1}	I _c =-10mA,I _b =-1mA	-0.65		-0.85	V
	V _{BE(sat)2}	I _c =-50mA,I _b =-5mA			-0.95	V
Transition frequency	f _T	V _{CE} =-20V,I _c =-10mA,f=100MHz	250			MHz
Collector capacitance	C _c	V _{CB} =-5V,I _e =0,f=1MHz			4.5	pF
Emitter capacitance	C _e	V _{EB} =-0.5V,I _c =0,f=1MHz			10	pF
Noise figure	NF	V _{CE} =-5V,I _c =-0.1mA,f=10Hz-15.7kHz, R _s =1KΩ			4	dB
Delay time	t _d	I _c =-10mA , I _{b1} =-I _{b2} = -1mA			35	ns
Rise time	t _r				35	ns
Storage time	t _s				225	ns
Fall time	t _f				75	ns

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